

N-Channel Super-junction MOSFET Gen I

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

650V Super-junction Gen I

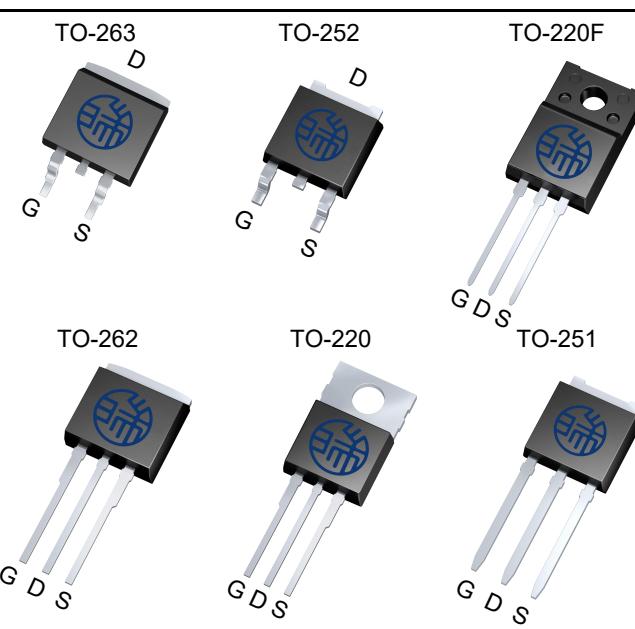
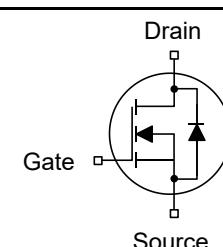
650V Super-junction Gen I Power Transistor

HRM65R400Fx Data Sheet

Rev. 2020 V1.0



650V Super-junction Power MOSFET Gen I

<p>Description</p> <p>650V Super-junction MOSFET Gen I</p> <p>Super-junction MOSFET Gen I is designed by HR-Micro Semiconductor Company, according to the SJ principle. This device provide an excellent Gate charge and Rds(on), which leads to extremely low communication and conduction losses. So it is very suitable for AC/DC power conversion, Laptop adapter, Lighting, and industrial power applications.</p>																								
<p>Features</p> <ul style="list-style-type: none"> Very low FOM $R_{DS(on)} \times Q_g$ 100% avalanche tested Ultra-fast body diode Easy to use/drive RoHS compliant 																								
<p>Applications</p> <ul style="list-style-type: none"> Switch Mode Power Supply (SMPS) Uninterruptible Power Supply (UPS) Power Factor Correction (PFC) Charger 	 																							
<p>Key Performance Parameters</p>																								
<table border="1"> <thead> <tr> <th>Parameter</th><th>Value</th><th>Unit</th></tr> </thead> <tbody> <tr> <td>$V_{DS} @ T_{j,max}$</td><td>700</td><td>V</td></tr> <tr> <td>$R_{DS(on),max}$</td><td>0.4</td><td>Ω</td></tr> <tr> <td>$Q_{g,typ}$</td><td>22.0</td><td>nC</td></tr> <tr> <td>I_D</td><td>11</td><td>A</td></tr> <tr> <td>$I_{D,pulse}$</td><td>33</td><td>A</td></tr> <tr> <td>$E_{oss} @ 400V$</td><td>2.22</td><td>μJ</td></tr> <tr> <td>Body Diode dI_F/dt</td><td>900</td><td>A/μs</td></tr> </tbody> </table>	Parameter	Value	Unit	$V_{DS} @ T_{j,max}$	700	V	$R_{DS(on),max}$	0.4	Ω	$Q_{g,typ}$	22.0	nC	I_D	11	A	$I_{D,pulse}$	33	A	$E_{oss} @ 400V$	2.22	μJ	Body Diode dI_F/dt	900	A/ μs
Parameter	Value	Unit																						
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I_D	11	A																						
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Body Diode dI_F/dt	900	A/ μs																						
<p>Device Marking and Package Information</p>																								
<table border="1"> <thead> <tr> <th>Device</th><th>Package</th><th>Marking</th></tr> </thead> <tbody> <tr> <td>HRM65R400FB</td><td>TO-263</td><td>65R400FB</td></tr> <tr> <td>HRM65R400FD</td><td>TO-252</td><td>65R400FD</td></tr> <tr> <td>HRM65R400FF</td><td>TO-220F</td><td>65R400FF</td></tr> <tr> <td>HRM65R400FL</td><td>TO-262</td><td>65R400FL</td></tr> <tr> <td>HRM65R400FP</td><td>TO-220</td><td>65R400FP</td></tr> <tr> <td>HRM65R400FU</td><td>TO-251</td><td>65R400FU</td></tr> </tbody> </table>	Device	Package	Marking	HRM65R400FB	TO-263	65R400FB	HRM65R400FD	TO-252	65R400FD	HRM65R400FF	TO-220F	65R400FF	HRM65R400FL	TO-262	65R400FL	HRM65R400FP	TO-220	65R400FP	HRM65R400FU	TO-251	65R400FU			
Device	Package	Marking																						
HRM65R400FB	TO-263	65R400FB																						
HRM65R400FD	TO-252	65R400FD																						
HRM65R400FF	TO-220F	65R400FF																						
HRM65R400FL	TO-262	65R400FL																						
HRM65R400FP	TO-220	65R400FP																						
HRM65R400FU	TO-251	65R400FU																						

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source voltage($V_{GS}=0\text{V}$)	V_{DS}	650	V
Continuous Drain Current ¹⁾	I_D	11	A
$T_C = 100^\circ\text{C}$		6.6	
Pulsed Drain Current ²⁾	$I_{D,\text{pulse}}$	33	A
Gate-Source Voltage	V_{GS}	$\pm 30\text{V}$	V
Single Pulse Avalanche Energy	E_{AS}	215	mJ
Repetitive Avalanche Energy	E_{AR}	0.32	mJ
Avalanche Current	I_{AR}	1.8	A
MOSFET dv/dt Ruggedness, $V_{DS} = 0 \dots 480\text{V}$	dv/dt	50	V/ns
Power Dissipation For TO-263、TO-252、TO-262、TO-220、TO-251	P_D	83	W
Power Dissipation For TO-220F		31	
Continuous Diode Forward Current	I_S	11	A
Diode Pulsed Current ²⁾	$I_{S,\text{pulse}}$	33	
Reverse Diode dv/dt ³⁾	dv/dt	50	V/ns
Maximum Diode Commutation Speed	di/dt	900	A/ μs
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	°C

Thermal Resistance For TO-263、TO-252、TO-262、TO-220、TO-251

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	1.5	°C/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	62	

Thermal Resistance For TO-220F

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	R_{thJC}	4	°C/W
Thermal Resistance, Junction-to-Ambient	R_{thJA}	80	

Notes

- 1) Limited by maximum junction temperature.
- 2) Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3) Identical low side and high side switch with identical R_G .

Electrical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Characteristics						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{GS} = 0V, I_D = 250\mu\text{A}$	650	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 650\text{V}$ $V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	μA
		$V_{DS} = 650\text{V},$ $V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	1000	
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 30\text{V}$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	3.0	4.0	5.0	V
Drain-Source On-State-Resistance	$R_{DS(\text{on})}$	$V_{GS} = 10\text{V}, I_D = 5.5\text{A}$	--	0.35	0.40	Ω
Gate Resistance	R_G	$f = 1.0\text{MHz}$ open drain	--	4.8	--	Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 100\text{V}$ $f = 1.0\text{MHz}$	--	803	--	pF
Output Capacitance	C_{oss}		--	28.7	--	
Reverse Transfer Capacitance	C_{rss}		--	2.1	--	
Total Gate Charge	Q_g	$V_{DD} = 520\text{V}, I_D = 11\text{A}$ $V_{GS} = 10\text{V}$	--	22.0	--	nC
Gate-Source Charge	Q_{gs}		--	7.3	--	
Gate-Drain Charge	Q_{gd}		--	8.6	--	
Gate Plateau Voltage	V_{Plateau}		--	6.6	--	V
Turn-on Delay Time	$t_{d(\text{on})}$	$V_{DD} = 400\text{V}, I_D = 11\text{A}$ $R_G = 15\Omega, V_{GS} = 10\text{V}$	--	15	--	ns
Turn-on Rise Time	t_r		--	25	--	
Turn-off Delay Time	$t_{d(\text{off})}$		--	80	--	
Turn-off Fall Time	t_f		--	35	--	
Drain-Source Body Diode Characteristics						
Body Diode Forward Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 5.5\text{A},$ $V_{GS} = 0V$	--	1.0	1.5	V
Reverse Recovery Time	t_{rr}	$V_R = 400\text{V}$ $I_F = 5.5\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$	--	115	--	ns
Reverse Recovery Charge	Q_{rr}		--	0.49	--	μC
Peak Reverse Recovery Current	I_{rrm}		--	8.5	--	A

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Transient Thermal Impedance
For TO-263/TO-252/TO-262/TO-220/TO-251

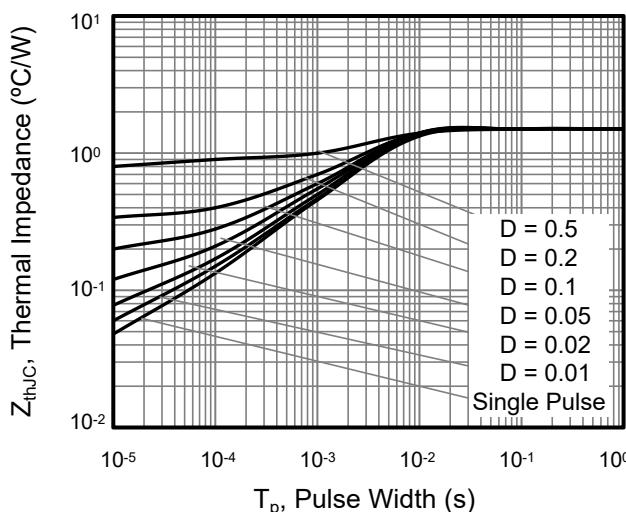


Figure 2. Transient Thermal Impedance
For TO-220F

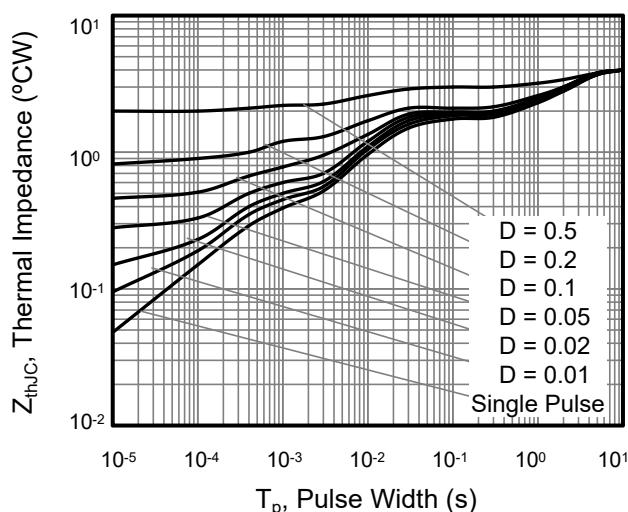


Figure 3. Safe Operation Area
For TO-263/TO-252/TO-262/TO-220/TO-251

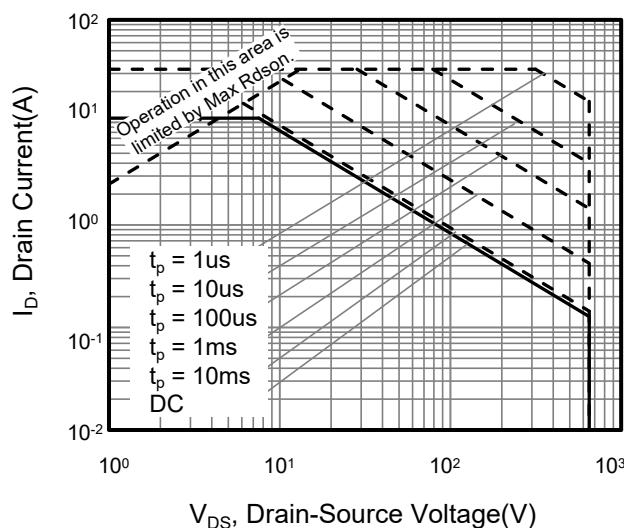


Figure 4. Safe Operation Area
For TO-220F

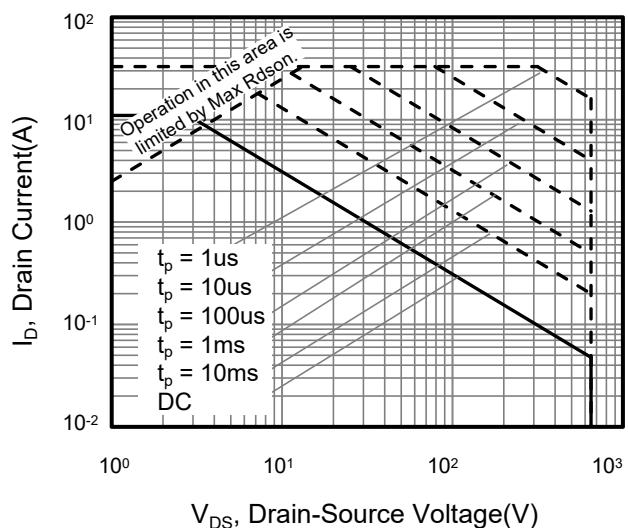


Figure 5. Output Characteristics

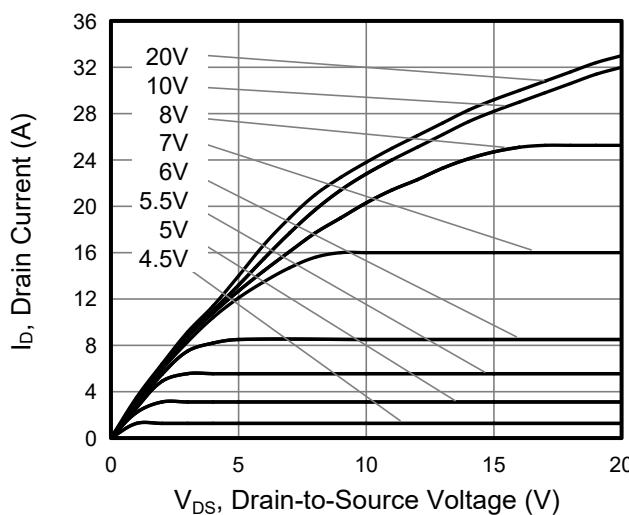
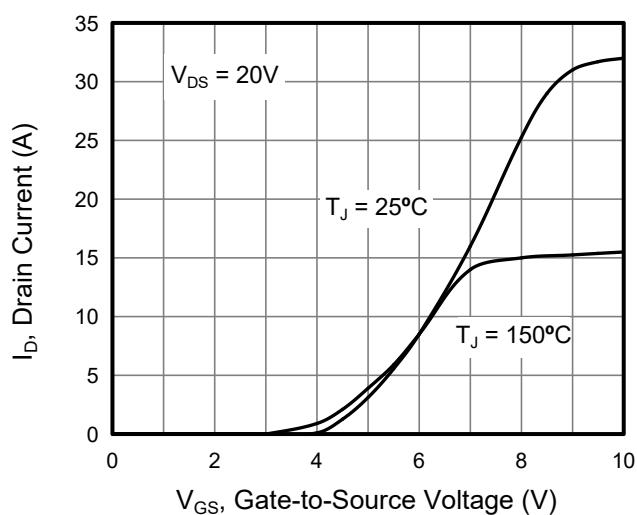


Figure 6. Transfer Characteristics



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. On-Resistance vs. Drain Current

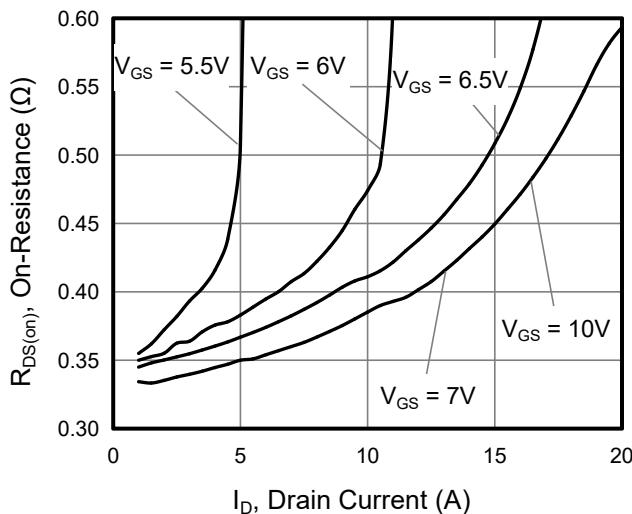


Figure 8. Capacitance

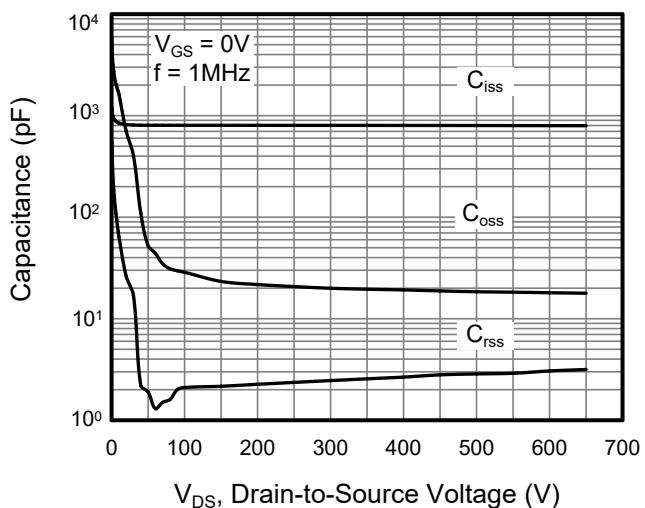


Figure 9. Gate Charge

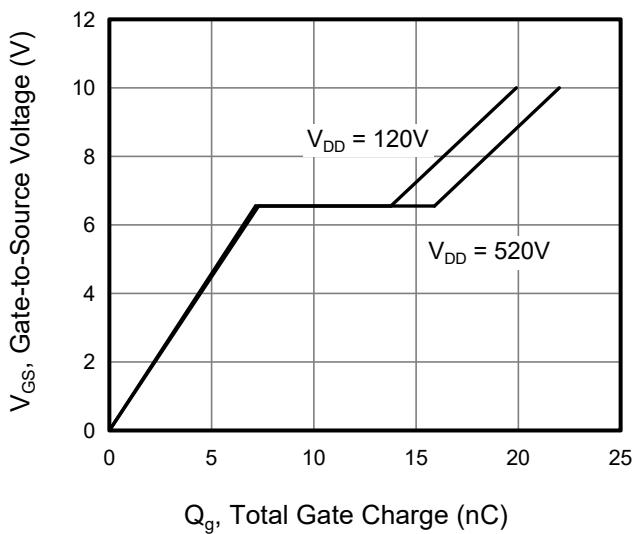


Figure 10. Body Diode Forward Voltage

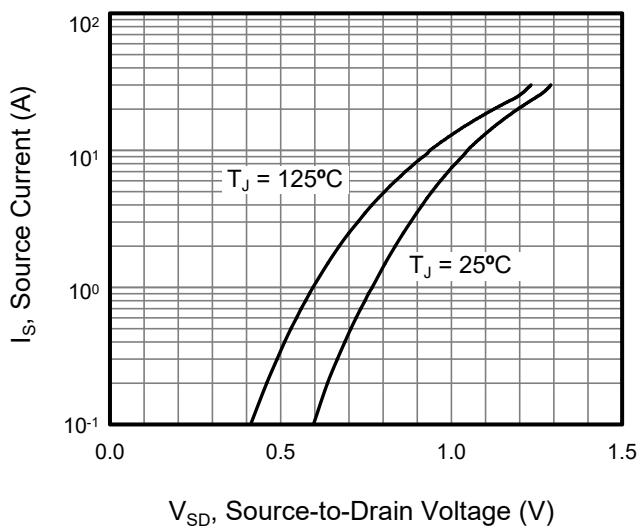


Figure 11. Typ. Coss Stored Energy

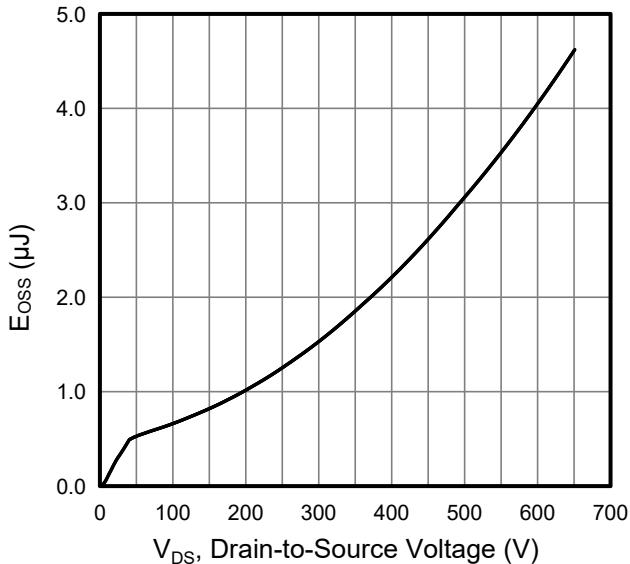
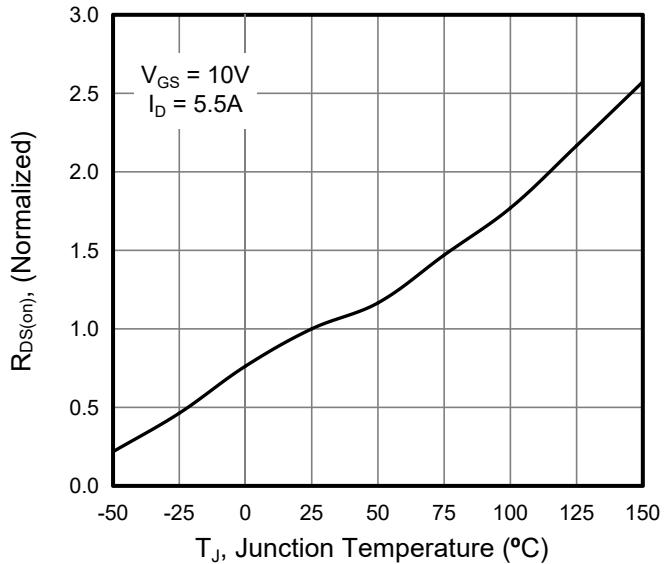


Figure 12. On-Resistance vs. Temperature



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 13. Breakdown Voltage vs.
Junction Temperature

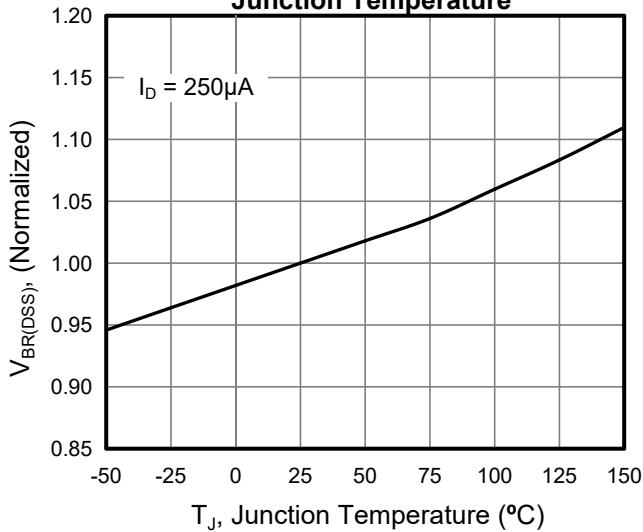


Figure A: Gate Charge Test Circuit and Waveform

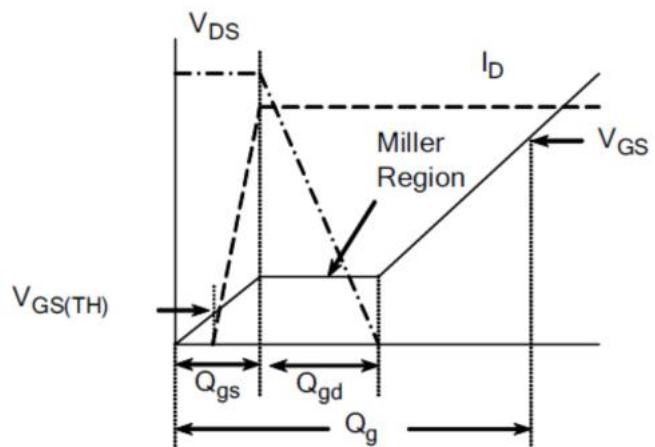
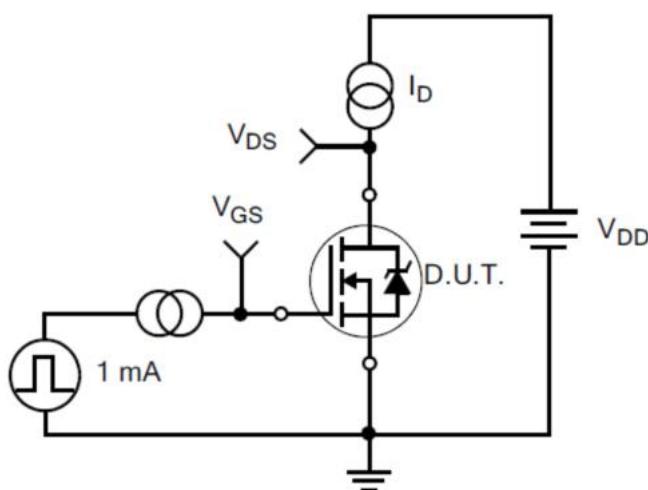


Figure B: Resistive Switching Test Circuit and Waveform

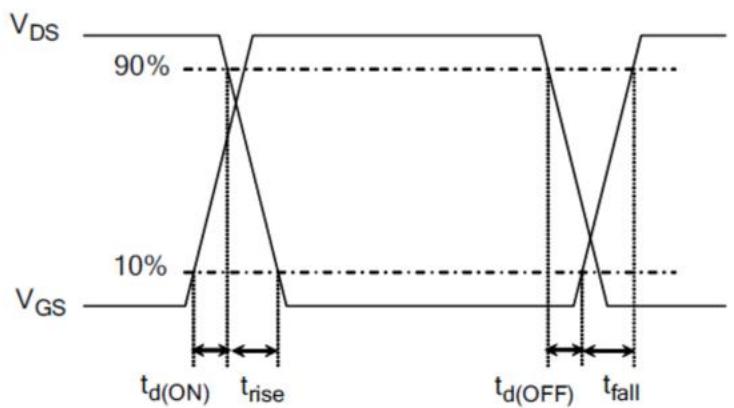
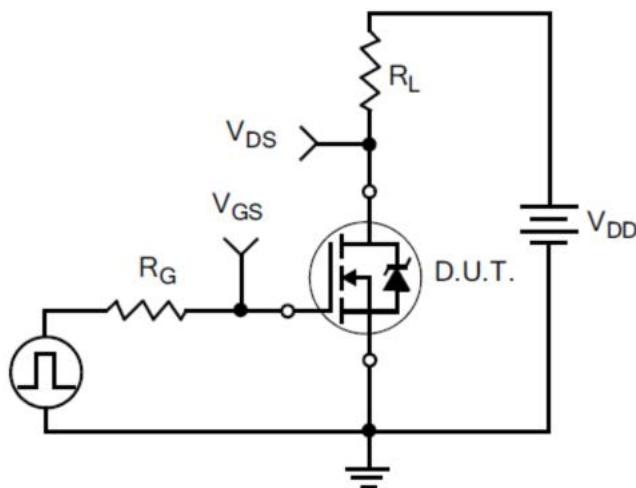
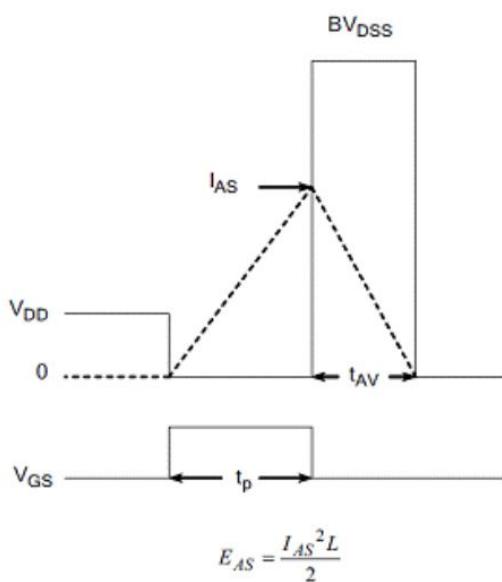
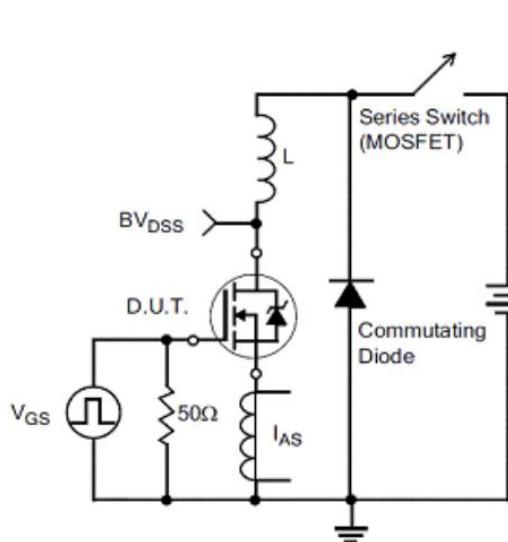
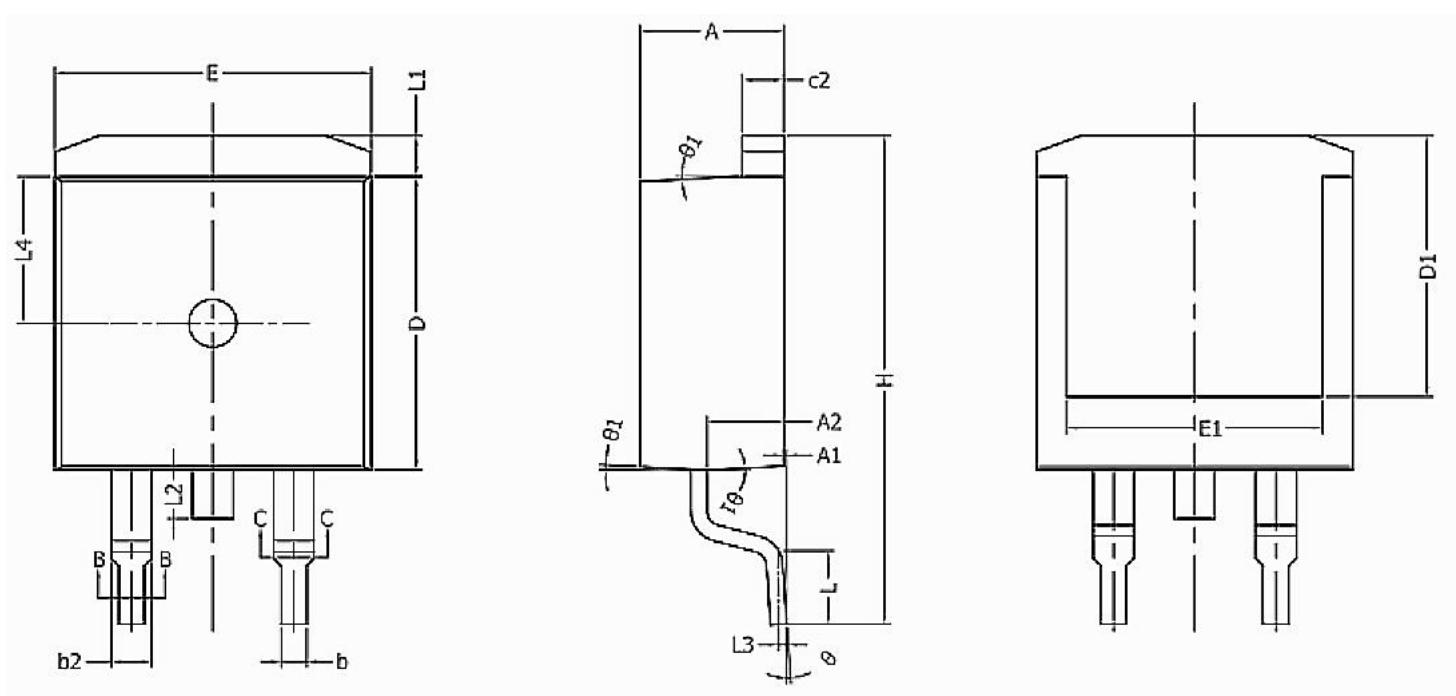


Figure C: Unclamped Inductive Switching Test Circuit and Waveform



TO-263



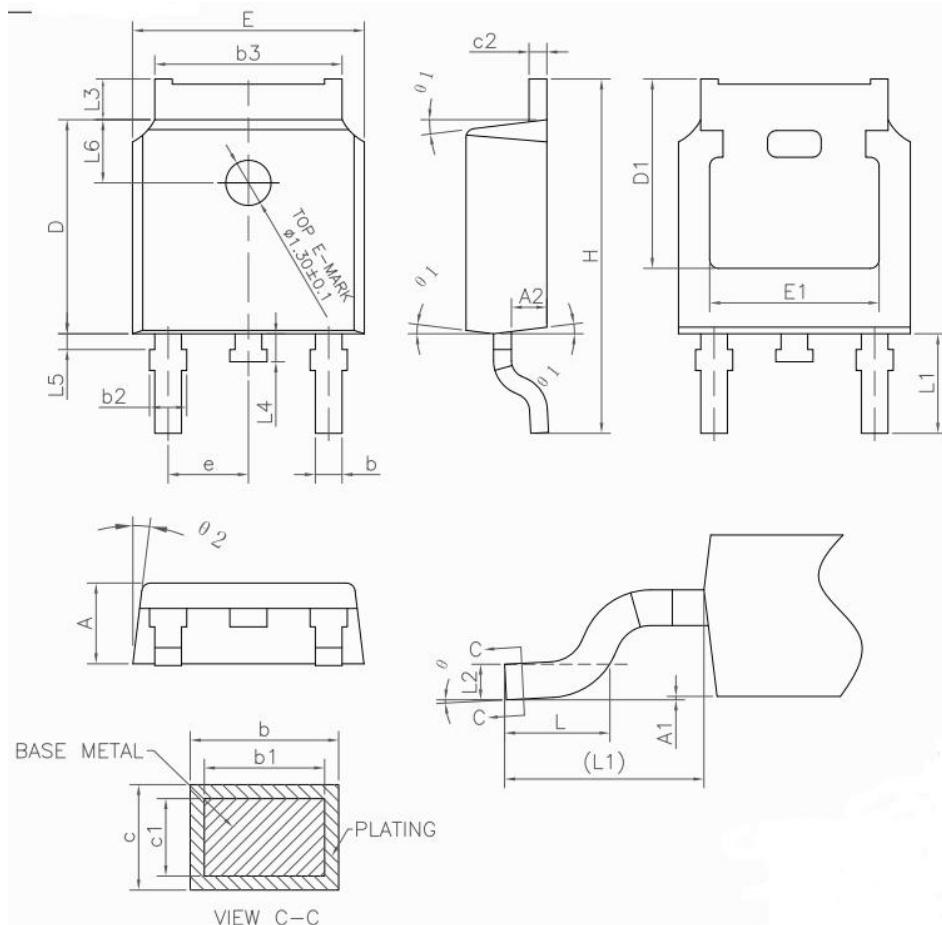
Unit:mm			
Symbol	Min.	Nom	Max.
A	4.40	4.50	4.60
A1	0	0.10	0.25
A2	2.20	2.40	2.60
b	0.76	---	0.89
b1	0.75	0.80	0.85
b2	1.23	---	1.37
b3	1.22	1.27	1.32
c	0.47	---	0.60
c1	0.46	0.51	0.56
c2	1.25	1.30	1.35
D	9.10	9.20	9.30

Unit:mm			
Symbol	Min.	Nom	Max.
D1	8.00	---	---
E	9.80	9.90	10.00
E1	7.80	---	---
e	2.54 BSC		
H	14.90	15.30	15.70
L	2.00	2.30	2.60
L1	1.17	1.27	1.40
L2	---	---	1.75
L3	0.25 BSC		
L4	4.60 REF		
θ	0°	---	8°
θ1	1°	3°	5°

Ordering information For TO-263

Package	Units/Tape	Tapes/ Inner Box	Units/Inner Box	Inner Box/Carton Box	Units/Carton Box
TO-263	800	1	800	10	8000

TO-252



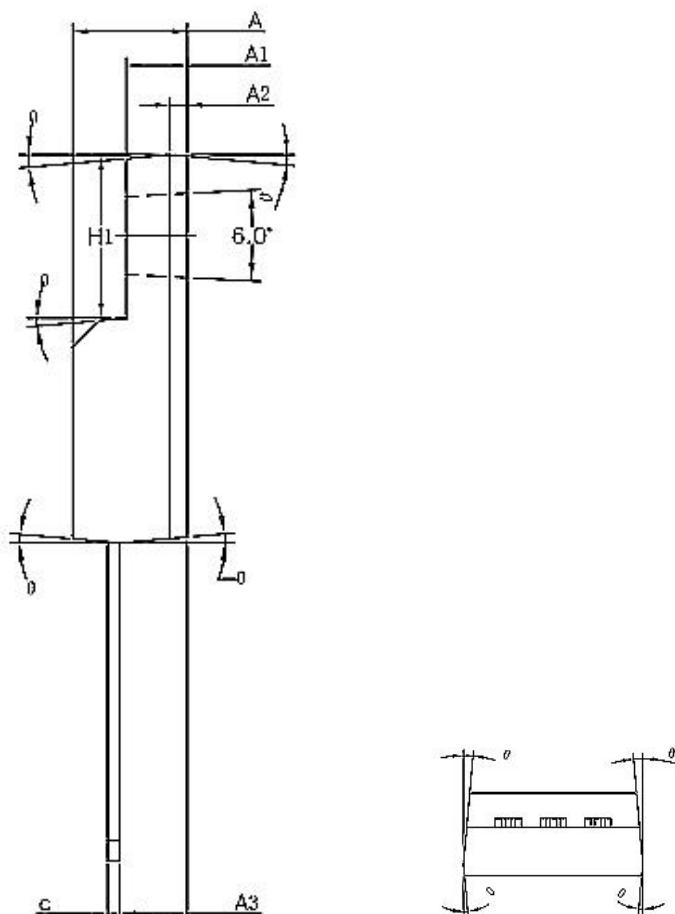
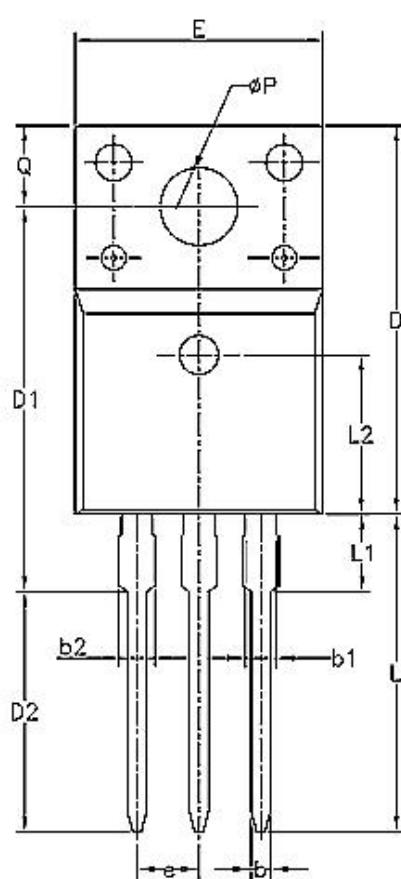
Unit:mm			
Symbol	Min.	Nom	Max.
A	2.20	2.30	2.38
A1	0.00	-	0.20
A2	0.90	1.01	1.10
b	0.72	--	0.85
b1	0.71	0.76	0.81
b2	0.72	--	0.90
b3	5.13	5.33	5.46
c	0.47	--	0.60
c1	0.46	0.51	0.56
c2	0.47	--	0.60
D	6.00	6.10	6.20
D1	5.25	--	--
E	6.50	6.60	6.70

Unit:mm			
Symbol	Min.	Nom	Max.
E1	4.70	--	--
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.508 BSC		
L3	0.90	--	1.25
L4	0.60	0.80	1.00
L5	0.15	--	0.75
L6	1.80 REF		
θ	0°	-	8°
θ1	5°	7°	9°
θ2	5°	7°	9°

Ordering information For TO-252

Package	Units/Tape	Tapes/ Inner Box	Units/Inner Box	Inner Box/Carton Box	Units/Carton Box
TO-252	2500	2	5000	5	25000

TO-220F



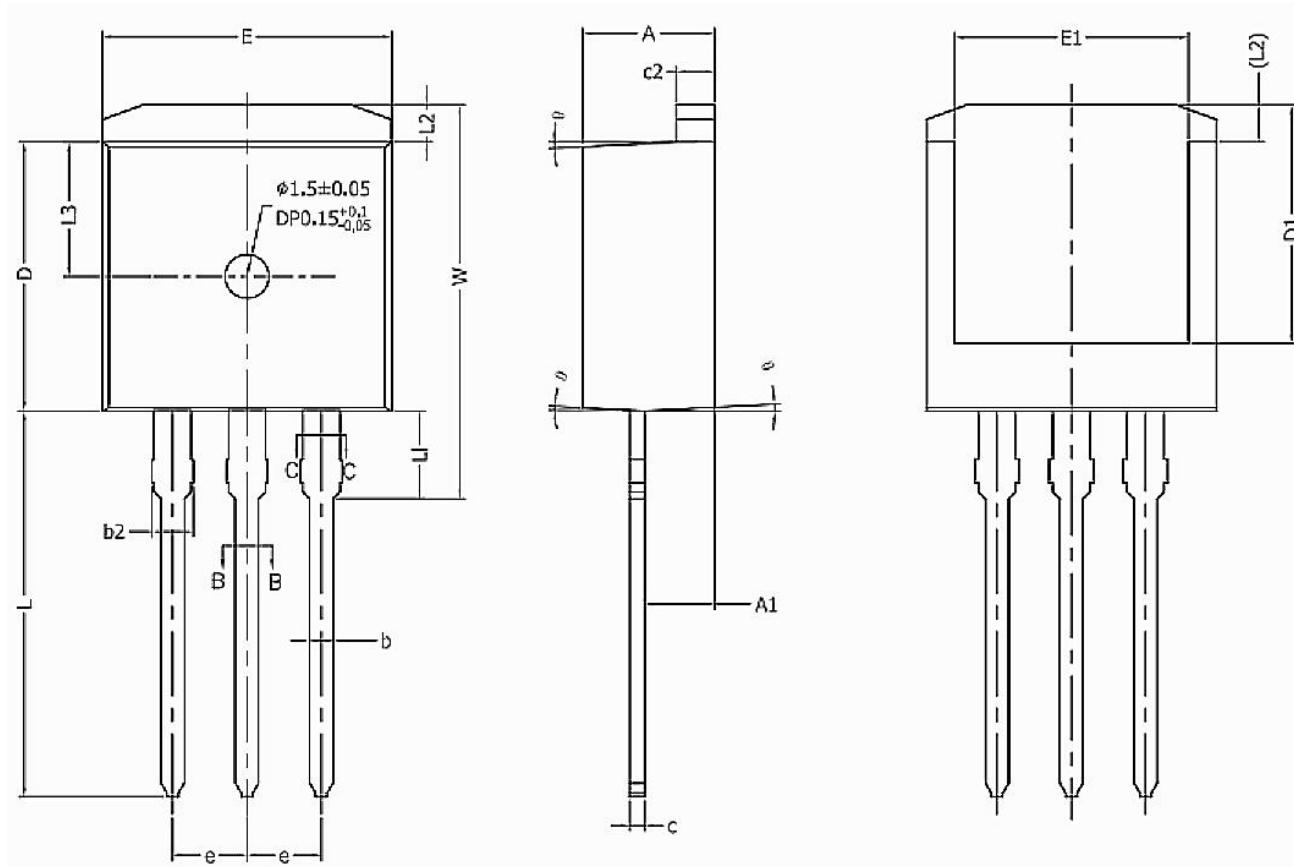
Unit:mm			
Symbol	Min.	Nom	Max.
A	4.50	4.70	4.83
A1	2.34	2.54	2.74
A2			0.70 REF
A3	2.56	2.76	2.93
b	0.70	---	0.90
b1	1.18	---	1.38
b2	---	---	1.47
c	0.45	0.50	0.60
D	15.67	15.87	16.07
D1	15.55	15.75	15.95

Unit:mm			
Symbol	Min.	Nom	Max.
D2	9.60	9.80	10.0
E	9.96	10.16	10.36
e			2.54 BSC
H1	6.48	6.68	6.88
L	12.68	12.98	13.28
L1	---	---	3.50
L2			6.50 REF
ΦP	3.08	3.18	3.28
Q	3.20	---	3.40
θ1	1°	3°	5°

Ordering information For TO-220F

Package	Units/Tube	Tubes/ Inner Box	Units/Inner Box	Inner Box/Carton Box	Units/Carton Box
TO-220F	50	40	2000	4	8000

TO-262



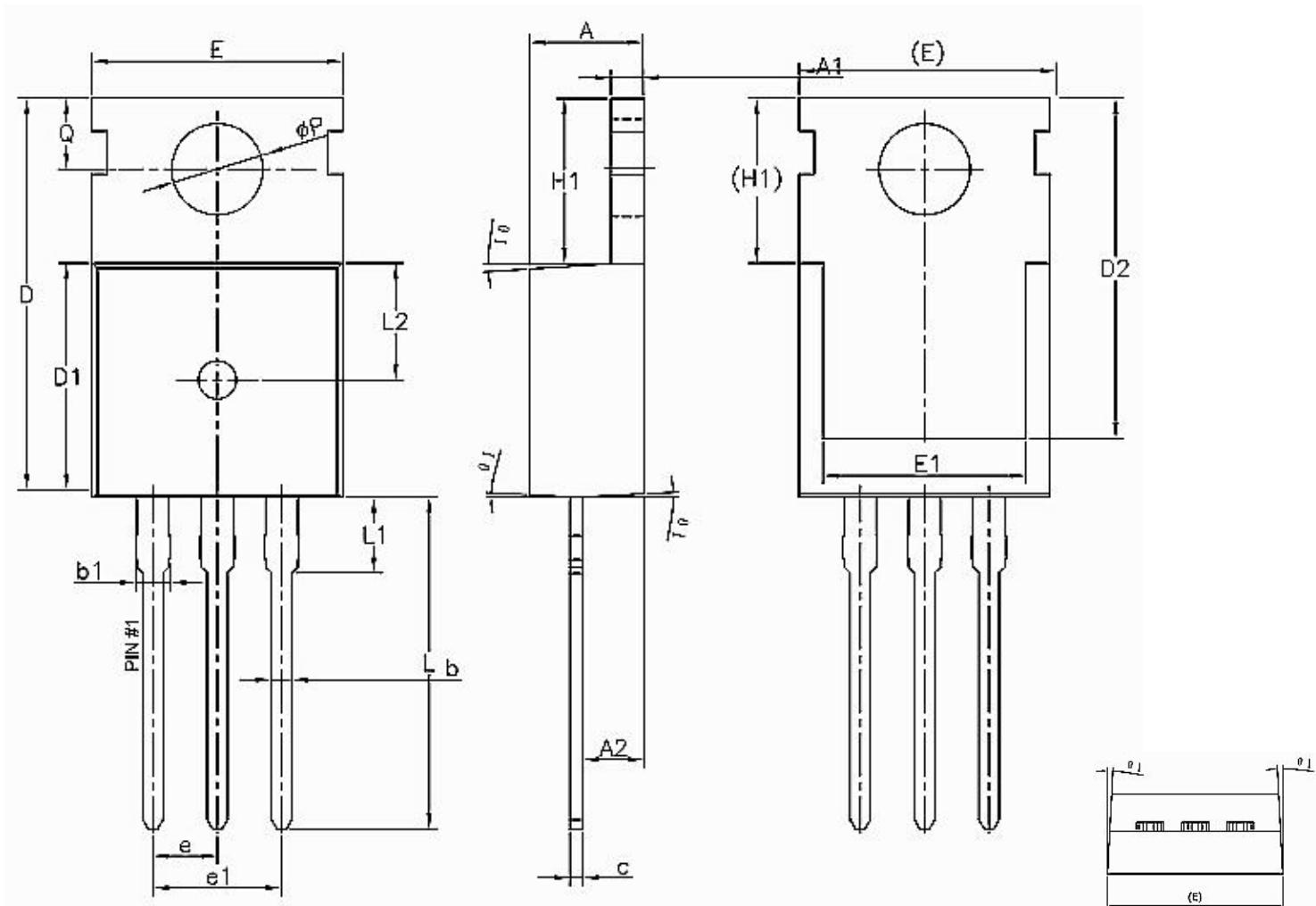
Unit:mm			
Symbol	Min.	Nom	Max.
A	4.40	4.50	4.60
A1	2.20	2.40	2.60
b	0.76	---	0.89
b1	0.75	0.80	0.85
b2	1.23	---	1.37
b3	1.22	1.27	1.32
c	0.47	---	0.60
c1	0.46	0.51	0.56
c2	1.25	1.30	1.35
D	9.10	9.20	9.30

Unit:mm			
Symbol	Min.	Nom	Max.
D1	8.00	---	---
E	9.80	9.90	10.00
E1	7.80	---	---
e	2.54 BSC		
L	12.90	13.20	13.50
L1	2.80	3.00	3.20
L2	1.17	1.27	1.40
L3	4.60 REF		
W	13.25	---	14.00
θ	1°	3°	5°

Ordering information For TO-262

Package	Units/Tube	Tubes/ Inner Box	Units/Inner Box	Inner Box/Carton Box	Units/Carton Box
TO-262	50	40	2000	4	8000

TO-220



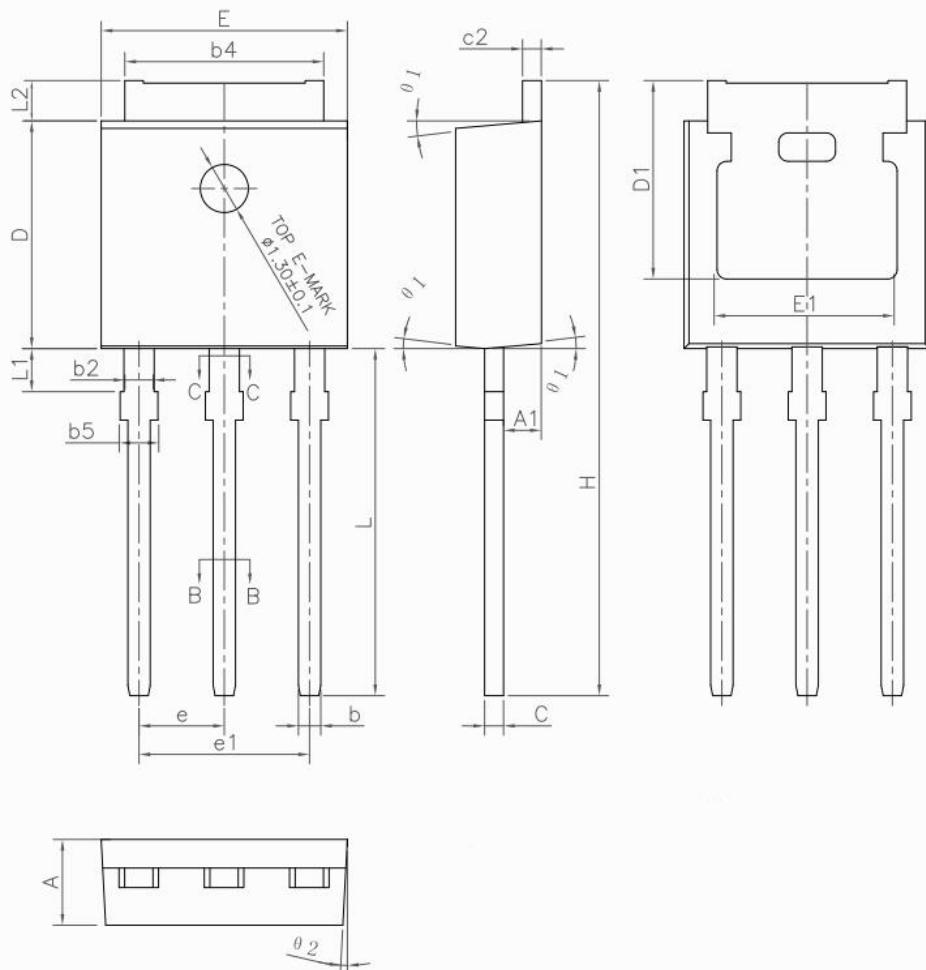
Unit:mm			
Symbol	Min.	Nom	Max.
A	4.40	4.50	4.60
A1	1.27	1.30	1.33
A2	2.30	2.40	2.50
b	0.70	---	0.90
b2	1.27	---	1.40
c	0.45	0.50	0.60
D	15.30	15.70	16.10
D1	9.10	9.20	9.30
D2	13.10	---	13.70
E	9.70	9.90	10.20

Unit:mm			
Symbol	Min.	Nom	Max.
E1	7.80	8.00	8.20
e	2.54 BSC		
e1	5.08 BSC		
H1	6.30	6.50	6.70
L	12.78	13.08	13.38
L1	---	---	3.50
L2	4.60 REF		
ΦP	3.55	3.60	3.65
Q	2.73	---	2.87
θ1	1°	3°	5°

Ordering information For TO-220

Package	Units/Tube	Tubes/ Inner Box	Units/Inner Box	Inner Box/Carton Box	Units/Carton Box
TO-220	50	40	2000	4	8000

TO-251



Unit:mm			
Symbol	Min.	Nom	Max.
A	2.20	2.30	2.35
A1	0.90	1.01	1.10
b	0.56	--	0.69
b1	0.55	0.60	0.65
b2	0.77	--	0.90
b3	0.76	0.81	0.86
b4	5.23	5.33	5.43
b5	--	--	1.05
c	0.46	--	0.59
c1	0.45	0.51	0.55
c2	0.46	--	0.59
D	6.00	6.10	6.20

Unit:mm			
Symbol	Min.	Nom.	Max.
D1	5.20	--	--
E	6.50	6.60	6.70
E1	4.60	4.83	5.00
e	2.24	2.29	2.34
e1	4.47	4.57	4.67
H	16.18	16.48	16.78
L	9.00	9.30	9.60
L1	0.95	1.16	1.35
L2	0.90	1.08	1.25
$\theta 1$	3°	5°	7°
$\theta 2$	1°	3°	5°

Ordering information For TO-251

Package	Units/Tube	Tubes/ Inner Box	Units/Inner Box	Inner Box/Carton Box	Units/Carton Box
TO-251	75	120	9000	4	36000

Disclaimer

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